

STC08IE150HV

Emitter Switched Bipolar Transistor ESBT[®] 1500 V - 8 A - 0.10 Ω

Features

V _{CS(ON)}	۱ _C	R _{CS(ON)}
0.8 V	8 A	0.10 Ω

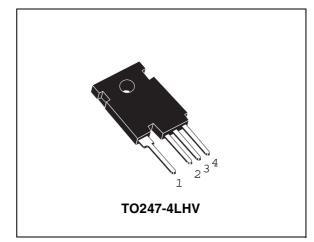
- High voltage / high current Cascode configuration
- Low equivalent on resistance
- Very fast-switch, up to 150 kHZ
- Squared rbsoa, up to 1500 V
- Very low C_{ISS} driven by $R_G = 47 \Omega$
- Very low turn-off cross over time
- In compliance with the 2002/93/EC European Directive

Applications

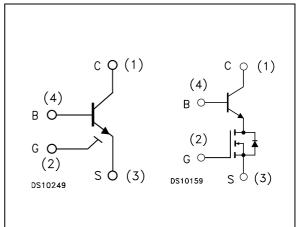
- Aux SMPS for three phase mains
- Sepic PFC

Description

The STC08IE150HV is manufactured in Monolithic ESBT Technology, aimed to provide best performance in high frequency / high voltage applications. it is designed for use in Gate Driven based topologies.



Internal Schematic Diagram



Order Codes

Part Number	Marking	Package	Packaging
STC08IE150HV C08IE150HV		TO247-4LHV	TUBE

December 2006

PRELIMINARY DATA

1 Absolute Maximum Ratings

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Symbol	Parameter	Value	Unit			
V _{CS(SS)}	Collector-source voltage ($V_{BS} = V_{GS} = 0 V$)	1500	V			
V _{BS(OS)}	Base-source voltage (I _C = 0, V _{GS} = 0 V)	30	V			
V _{SB(OS)}	source-base voltage ($i_c = 0$, $v_{gs} = 0$ v)	17	V			
V _{GS}	Gate-source Voltage	± 17	V			
۱ _C	Collector Current	8	Α			
I _{CM}	Collector peak current (t _P < 5ms)	24	Α			
Ι _Β	Base current	6	Α			
I _{BM}	Base peak current (t _P < 1ms)	12	А			
P _{tot}	Total dissipation at $T_c = 25^{\circ}C$	208	W			
T _{stg}	Storage temperature	-40 to 150	°C			
ТJ	Max. operating junction temperature	150	°C			

Table 1. Absolute Maximum Ratingsn

1.1 Thermal Data

Table 2. Thermal Data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case Max	0.6	°C/W



2 Electrical Characteristics

Symbol	Parameter	Test Cor	nditions	Min.	Тур.	Max.	Unit
I _{CS(SS)}	Collector-source current $(V_{BS} = V_{GS} = 0)$	V _{CE} = 1500V				100	μA
I _{BS(OS)}	Base-source current (I _C = 0, V _{GS} = 0 V)	$V_{BS(OS)} = 30V$				10	μA
I _{SB(OS)}	Source-base current (I _C = 0, V _{GS} = 0)	$V_{SB(OS)} = 17V$				100	μA
I _{GS(OS)}	Gate-source leakage	$V_{GS} = \pm 17V$				100	nA
V _{CS(ON)}	Collector-source ON voltage	$V_{GS} = 10V I_C = 8V$ $V_{GS} = 10V I_C = 3V$			1 0.7	1.5 1.2	V V
h _{FE}	DC current gain	$V_{GS} = 10V V_{CS} = V_{GS} = 10V V_{CS} =$	-	4.5 9	6 11		
V _{BS(ON)}	Base-source ON voltage	$V_{GS} = 10V I_{C} = 8i$ $V_{GS} = 10V I_{C} = 2i$	-		1.6 1.1	2 1.5	V V
V _{GS(th)}	Gate threshold voltage	$V_{BS} = V_{GS}$	I _B = 250 μA	2	3	4	V
C _{ISS}	Input capacitance	V _{CS} =25V V _{GS} =V _{CB} =0V	f =1MHz		810		pF
Q _{GS(tot)}	Gate-source charge	V _{CS} =15V V _{CB} =0V	V _{GS} =10V I _C =1.4A		45.6		nC
t _s t _f	INDUCTIVE LOAD Storage time Fall time	$V_{GS} = 10V$ $V_{Clamp} = 1200V$ $I_{C} = 4A$	R _G =47Ω t _p =4μs I _B =0.8A		690 10		ns ns
t _s t _f	INDUCTIVE LOAD Storage time Fall time	$V_{GS} = 10V$ $V_{Clamp} = 1200V$ $I_{C} = 4A$	R _G =47Ω t _p =4μs I _B =0.4A		340 10		ns ns
V _{CS(dyn)}	Collector-source dynamic voltage (500ns)	$V_{CC} = V_{Clamp} = 600$ $V_{GS} = 10V$ $I_B = 0.4A$ $t_{peak} = 500$ ns	I _C =2A		2.8		v
V _{CS(dyn)}	Collector-source dynamic voltage (1µs)	$V_{CC} = V_{Clamp} = 600$ $V_{GS} = 10V$ $I_B = 0.4A$ $t_{peak} = 500ns$	V I _C =2A R _G =47Ω I _{Bpeak} =4A		1.7		v
V _{CSW}	Maximum collector-source voltage switched without snubber	$R_G = 47\Omega$ $I_C = 8A$	h _{FE} =5	1500			v

Table 3.	Electrical Characteristics (T _{CASE} = 25°C; unless other	wise specified)
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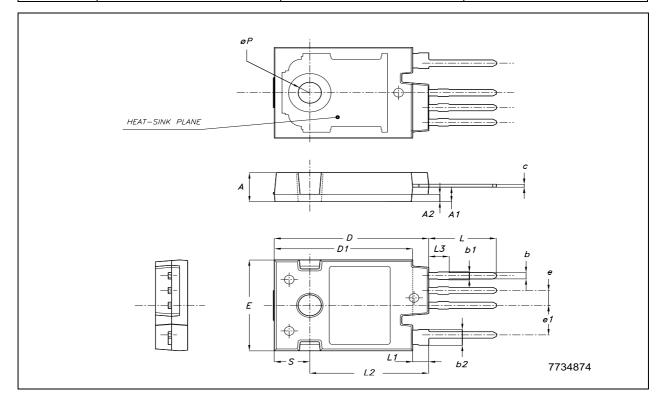
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



TO247-4LHV MECHANICAL DATA

DIM.		mm.	
	MIN.	ТҮР	MAX.
A	4.85		5.15
A1	2.20	2.50	2.60
A2		1.27	
b	0.95	1.10	1.30
b2	2.50		2.90
с	0.40		0.80
D	23.85	24	24.15
D1		21.50	
E	15.45	15.60	15.75
е	2.54		
e1	5.08		
L	10.20		10.80
L1	2.20	2.50	2.80
L2		18.50	
L3		3	
ØP	3.55		3.65
S		5.50	



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4 Revision History

Date	Revision	Changes	
30-Jan-2006	1	Initial release.	
01-Dec-2006	2	The document has been reformatted	



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